

forming a photoresist pattern on the metal layer, such that a portion of the metal layer is exposed;

Cont'd  
D1  
treating the exposed portion of the metal layer with a first plasma, prior to any step of etching said photoresist pattern, and prior to any step of etching said metal layer, using the photoresist pattern as a mask, to lower a binding force in the exposed portion; and

etching the treated portion of the metal layer to form a pixel electrode.

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22. (Three Times Amended) A method of patterning a metal layer, comprising:

depositing a metal layer over a substrate;

D2  
forming a mask on the metal layer, leaving a portion of the metal layer uncovered;

exposing the uncovered portion of the metal layer to a first plasma, prior to any step of etching said mask, and prior to any step of etching said metal layer, to lower a binding force in the uncovered portion; and

etching the uncovered portion of the metal layer with a second plasma to form a metal pattern.

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30. (Twice Amended) A method of manufacturing a pixel electrode in a liquid crystal display device, comprising:

depositing a metal layer on a passivation layer which partially covers a transistor;

forming a photoresist pattern on the metal layer, leaving a portion of the metal layer uncovered;

23 exposing the uncovered portion of the metal layer to at least one first gas, prior to any step of etching said photoresist pattern and prior to any step of etching said metal layer, to lower a binding force in the uncovered portion; and

etching the uncovered portion of the metal layer with at least one second gas to form a pixel electrode.

31. (Amended) A method of manufacturing a pixel electrode in a liquid crystal display device, comprising:

depositing a metal layer on a passivation layer which partially covers a transistor;

forming a photoresist pattern adjacent to the metal layer, leaving a portion of the metal layer uncovered;

cont'd  
D3  
exposing the uncovered portion of the metal layer to at least one first  
gas, prior to any step of etching, to lower a binding force in the uncovered  
portion; and

etching the uncovered portion of the metal layer with at least one second  
gas to form a pixel electrode.

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